

ABSTRACT OF THE DISCLOSURE

A method for the fabrication of a field-effect transistor wherein after forming a semiconductor layer serving as an active layer on a substrate, the substrate temperature is set at no higher than 100°C, a gate insulating film is formed on the semiconductor layer. Then, the gate insulating film is heat treated in an atmosphere containing water. By heat treating in the atmosphere containing water, OH bonds in the vicinity of the insulating film interface are reduced and, therefore, the CV characteristic thereof is improved.

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